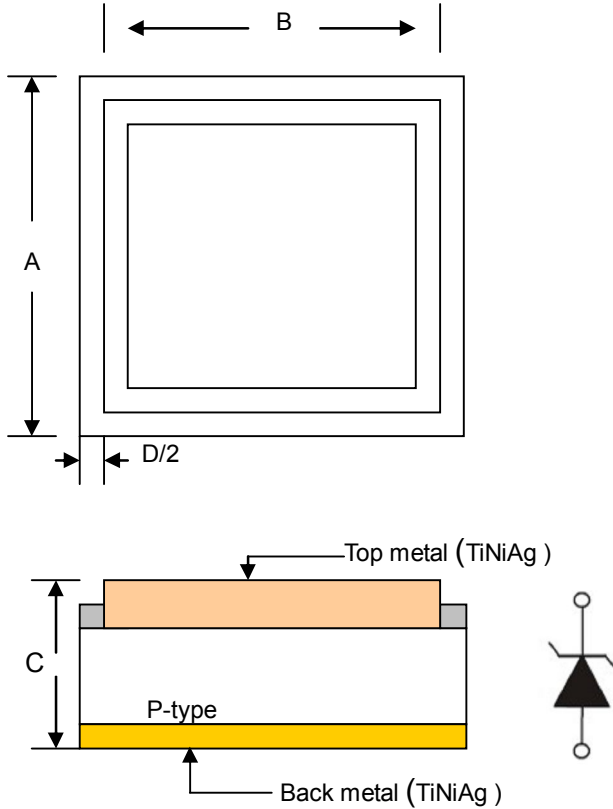


200W Planar TVS



Item	Dimensions	
	um	mil
Die Size (A)	990	39
Top Metal (Ag)	925	36.4
Top Metal Pad size (B)		
Wafer Thickness (C)	250±20	9.84
Scribe Line Width (D)	50	1.96
Other Information		
Wafer Size	6"	
Gross Die	16800	
Back Side Metal	TiNiAg	

Absolute Maximum Ratings (Ta=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power Dissipation with a 10/1000 μ s Waveform	P _{PPM}	200	W
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 30	KV
ESD per IEC 61000-4-2 (Contact)		± 30	
Peak Forward Surge Current 8.3ms Single Half Sine-wave	I _{FSM}	25	A
Operating Junction and Storage Temperature Range	T _j T _{stg}	-55 to +150	°C

200W Planar TVS (Electrical Characteristics @TA=25°C)

品名	Reverse Stand-off Voltage	Breakdown Voltage		Test Current	Reverse Leakage	Max Clamp Voltage 10/1000us	Peak Pulse Current 10/1000us
	V _{RWM}	V _{BR}		I _T	I _R @ V _{RWM}	V _c @ I _{pp}	I _{pp}
		Min[V]	Max[V]	[mA]	[uA]	[V]	[A]
CS39S3P3HG	3.3	5.22	5.98	10	30	8.5	23.5
CS39S5P0HG	5.0	6.42	6.98	10	15	9.2	21.7
CS39S6P0HG	6.0	6.69	7.35	10	5	10.3	19.7
CS39S6P5HG	6.5	7.24	7.96	10	5	11.2	17.9
CS39S7P0HG	7.0	7.80	8.58	10	5	12	16.7